



Mark T. Ramsbey, Robert B. Ogle, Tommy C. Hsiao, Angela T. Hui

Tuan Duc Pham, Marina V. Plat and Lewis Shen

Assignee: Advanced Micro Devices, Inc.

Title: Polished Flash Process With Metal Gates And Improved Planarity

Serial No.: 09/430,366 Filing Date: October 28, 1999

Examiner: Chen, Jack Group Art Unit: 2813

Docket No.: M-7523 US

San Jose, California May 29, 2002

BOX RCE COMMISSIONER FOR PATENTS Washington, D. C. 20231

RESPONSE TO OFFICE ACTION (FINAL)

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Dear Sir:

This is a response to the Final Office Action dated February 12, 2002, which has a statutorily shortened period that ends on May 12, 2002. A one-month extension of time accompanies this Response, allowing the Applicants until June 12, 2002 to respond. Please enter the following amendments before taking action on the merits of the above-referenced application.

IN THE CLAIMS

The following is a clean version of the entire set of pending Claims 1, 3-7, 9-12, 14, 15 and 21-23. Claims 16-20 were withdrawn from consideration. In accordance with 37 CFR § 1.121(c)(1)(ii), an attachment provides marked up versions of the amended claims containing the newly introduced changes. Claims 7 and 21-23 are presently amended.

LAW OFFICES OF SKJERVEN MORRILL LLP 25 METRO DRIVE SLUTE 700

SAN JOSE, CA 95110 (408) 453-9200 FAX (408) 453 7979

US) 1.

(Thrice amended)

A method of making a flash memory cell including a

substrate and a floating gate, the method comprising:

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-1-

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